

JHB30N60EE2/JHG30N60EE2/ JHH30N60EE2/JHP30N60EE2

Product Preview

600V 30A FIELD-STOP TRENCH IGBT WITH DIODE

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Features

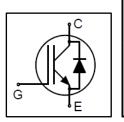
- Low V_{CE(sat)}
- Fast Switching
- High Ruggedness
- Short-Circuit Rated

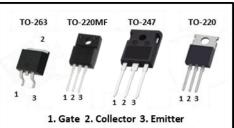


Product Summary						
V _{CES}	600V					
I _C	30A					
V _{CE(sat),typ.}	1.6V (T _J = 25°C)					
Package	JHB30N60EE2: TO-263 JHG30N60EE2: TO-220MF JHH30N60EE2: TO-247 JHP30N60EE2: TO-220					

Applications

- Motor Control
- Servo
- Home Appliances
- General Purpose Inverters





Ordering Information

Part Number	Marking	Package	Packing
JHB30N60EE2	HB30N60EE2	TO-263	Tube
JHB30N60EE2_R	HB30N60EE2	TO-263	Tape and reel
JHG30N60EE2	HG30N60EE2	TO-220MF	Tube
JHH30N60EE2	HH30N60EE2	TO-247	Tube
JHP30N60EE2	HP30N60EE2	TO-220	Tube

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Absolute Maximum Ratings

Parameter	Symbol	Limit	Unit	
Collector-to-Emitter Voltage	V _{CES}	600	v	
Gate-to-Emitter Voltage	V _{GES}	±20	v	
DC Collector Current	TO-263, TO-247, TO-220		30	
$(T_c = 90^{\circ}C, limited by max T_J)$	TO-220MF	I _C	21.5	
Pulsed Collector Current (pulse width limited by ma	Pulsed Collector Current (pulse width limited by max T _J)			
Diode Forward Current	TO-263, TO-247, TO-220		23.5	A
$(T_c = 90^{\circ}C, limited by max T_J)$	TO-220MF	I _F	15.5	
Diode Pulsed Current (pulse width limited by max 1	Г ₁)	I _{FM}	90	
Maximum Power Dissipation	TO-263, TO-247, TO-220	6	147	
(T _c = 25°C, T _J = 150°C)	P _{D(max)}	89	W	
Operating Junction Temperature	Tj	-40 to +150	°C	
Storage Temperature		T _{stg}	-40 to +150	

Static Electrical Characteristics (1)

Parameter	Symbol	Test Conditions	Min	Тур.	Max	Unit
Collector-to-Emitter Breakdown Voltage	BV _{CES}	V _{GE} = 0V, I _C = 250μA	600	-	-	V
		$V_{CE} = 600V, V_{GE} = 0V$	-	-	10	
Collector-to-Emitter Leakage Current	I _{CES}	V _{CE} = 600V, V _{GE} = 0V T _J = 150°C	-	-	250	μΑ
Gate-to-Emitter Leakage Current	I _{GES}	$V_{CE} = 0V, V_{GE} = \pm 20V$	-	-	100	nA
Gate Threshold Voltage	V _{GE(th)}	$V_{CE} = V_{GE}$, $I_C = 250 \mu A$	5.0	6.0	7.0	V
		V _{GE} = 15V, I _C = 30A	-	1.6	1.9	
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	V _{GE} = 15V, I _C = 30A, T _J =150°C	-	2.0	-	V
		$V_{GE} = 0V, I_F = 30A$	-	1.9	2.5	
Diode Forward Voltage	V _F	V _{GE} = 0V, I _F = 30A T _J =150°C	-	1.65	-	V



Thermal Characteristics

Parameter		Min	Тур	Max	Unit
Junction-to-Ambient Thermal Resistance (TO-263, TO-220)		-	-	62	
Junction-to-Ambient Thermal Resistance (TO-220MF)	Inction-to-Ambient Thermal Resistance (TO-220MF) R _{BJA}		-	65	
Junction-to-Ambient Thermal Resistance (TO-247)		-	-	40	
Junction-to-Case Thermal Resistance (TO-263, TO-247, TO-220), IGBT	ase Thermal Resistance (TO-263, TO-247, TO-220), IGBT		-	0.85	°C/W
Junction-to-Case Thermal Resistance (TO-263, TO-247, TO-220), Diode		-	-	1.4	
Junction-to-Case Thermal Resistance (TO-220MF), IGBT	R _{θJC}	-	-	1.4	
Junction-to-Case Thermal Resistance (TO-220MF), Diode		-	-	2.4	

Dynamic Electrical Characteristics (1)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Total Gate Charge	Qg	V _{CC} = 400V, V _{GE} = 15V, I _C = 30A	-	61	-	nC
Input Capacitance	C _{iss}	V = 25V	-	1458	-	
Output Capacitance	C _{oss}	$V_{CE} = 25V,$ $V_{GE} = 0V,$	-	98	-	pF
Reverse Transfer Capacitance	C _{rss}	f = 1MHz	-	30	-	



Switching Characteristics, Inductive Load $^{(1), (2)}$

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Turn-on delay time	t _{d(ON)}		-	27	-	
Rise Time	t _r	V _{CC} = 400V, V _{GE} = 0/15V,	-	38	-	20
Turn-off delay time	t _{d(OFF)}	$R_{G} = 10\Omega$,	-	88	-	ns
Fall Time	t _f	I _C = 30A, L _{load} = 0.82mH	-	75	-	
Turn-On Switching Loss	E _{on}	(Energy losses include "tail" and FRD reverse	-	0.65	-	
Turn-Off Switching Loss	E _{off}	recovery)	-	0.55	-	mJ
Total Switching Loss	E _{ts}		-	1.2	-	
Short Circuit Capability	t _{sc}	V _{GE} = 15V, V _{CC} ≤ 400V,	5	-	-	μs
Short Circuit Collector Current	I _{C(SC)}	V _{CC} ≤ 400V, V _P ≤ 600V	-	130	-	A

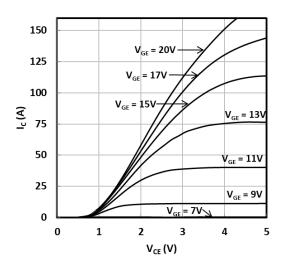
(1) $T_J = 25^{\circ}C$ unless otherwise specified.

(2) t_{r} : from 10% of Ic to 90% of Ic; t_{f} : from 90% of Ic to 10% of Ic;

 $E_{on}{:}$ from 10% of V_{GE} to 10% of $V_{CE}{;}\;\;E_{off}{:}$ from 90% of V_{GE} to 10% of Ic.



Typical Electrical Characteristics





(T_J = 25 °C, t_p = 250 μs)

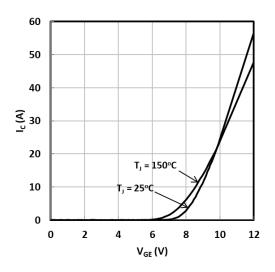


Fig. 3 Typical transfer characteristics $(V_{CE} = 10 \text{ V}, t_p = 250 \text{ } \mu\text{s})$

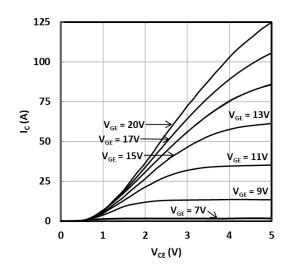


Fig. 2 Typical output characteristics

 $(T_J = 150 \ ^{\circ}C, t_p = 250 \ \mu s)$

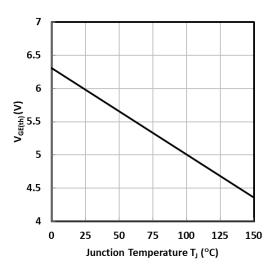


Fig. 4 Typical gate threshold voltage as a function of junction temperature $(V_{CE} = V_{GE} \text{ , } I_C = 250 \text{ } \mu\text{A})$



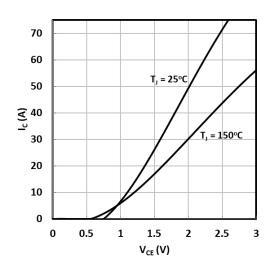
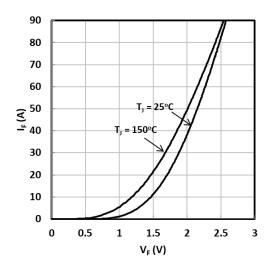
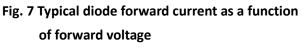


Fig. 5 Typical saturation voltage characteristics

$(V_{GE} = 15 V, t_p = 250 \mu s)$





(V_{GE} = 0 V, t_p = 250 µs)

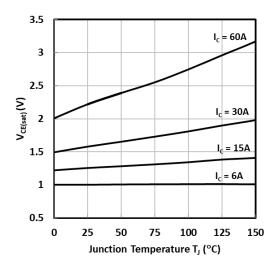
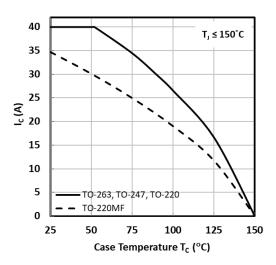
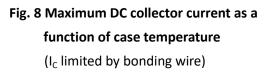


Fig. 6 Typical saturation voltage as a function of junction temperature

 $(V_{GE} = 15 V, t_p = 250 \mu s)$





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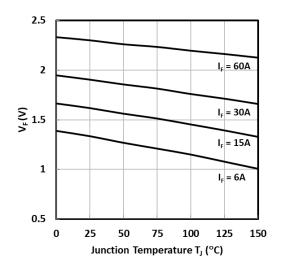


Fig. 9 Typical diode forward voltage as a function of junction temperature

 $(V_{GE} = 0 V, t_p = 250 \mu s)$

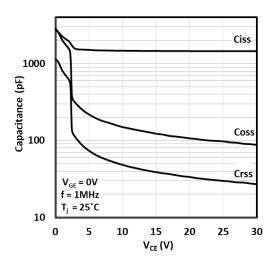


Fig. 11 Typical capacitance as a function of collector-to-emitter voltage

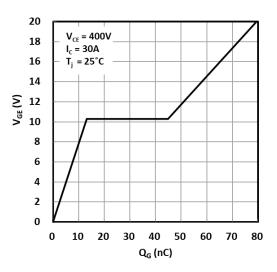
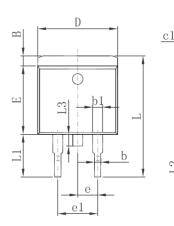


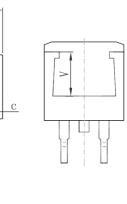
Fig. 10 Typical gate charge characteristics

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Package Drawing



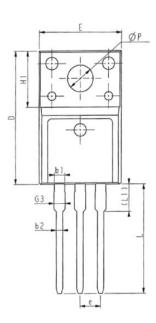


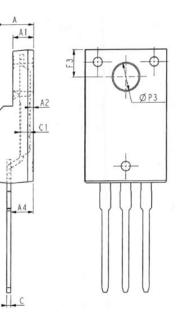
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Symbol	Dimensions In Millimeters			
Symbol	Min.	Max.		
А	4.470	4.670		
A1	0.000	0.150		
В	1.120	1.420		
b	0.710	0.910		
b1	1.170	1.370		
С	0.310	0.530		
c1	1.170	1.370		
D	10.010	10.310		
Е	8.500	8.900		
е	2.540	TYP.		
e1	4.980	5.180		
L	14.940	15.500		
L1	4.950	5.450		
L2	2.340	2.740		
L3	1.300	1.700		
Φ	0°	8°		
V	5.600	REF.		

TO-263

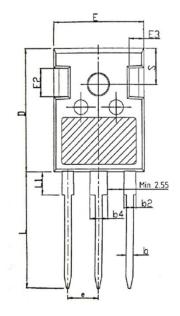




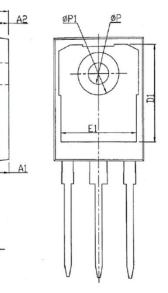
evanor		MM	
SYMBOL	MIN	NOM	MAX
E	9.96	10.16	10.36
Α	4.50	4.70	4.90
A1	2.34	2.54	2.74
A2	0.30	0.45	0.60
A4	2.56	2.76	2.96
С	0.40	0.50	0.65
c1	1.20	1.30	1.35
D	15.57	15.87	16.17
H1		6. 70REF	
е		2.54BSC	
L	12.68	12.98	13.28
L1	3.03	3.23	3.43
ΦP	3.03	3.18	3.38
ΦΡ3	3.15	3.45	3.65
F3	3.15	3.30	3.45
G3	1.25	1.35	1.55
b1	1.18	1.28	1.43
b2	0.70	0.80	0.95

TO-220MF



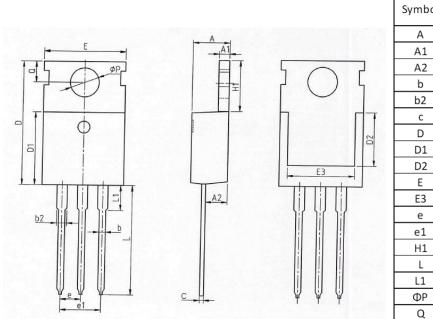


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	Din	nension (m	ım)
Symbol	Min.	Тур.	Max.
А	4.80	5.00	5.20
A1	2.21	2.41	2.59
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
b4	2.91	3.01	3.21
С	0.51	0.61	0.75
D	20.80	21.00	21.30
D1	16.25	16.55	16.85
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
е		5.44BSC	
L	19.62	19.92	20.22
L1	-	-	4.30
ФР	3.40	3.60	3.80
ΦΡ1	-	-	7.30
S		6.15BSC	

TO-247



Sumbol	Din	nension (m	ım)
Symbol	Min.	Тур.	Max.
А	4.37	4.57	4.70
A1	1.25	1.30	1.40
A2	2.20	2.40	2.60
b	0.70	0.80	0.95
b2	1.17	1.27	1.47
С	0.45	0.50	0.60
D	15.10	15.60	16.10
D1	8.80	9.10	9.40
D2	5.50	-	-
E	9.70	10.00	10.30
E3	7.00	-	-
е		2.54BSC	
e1		5.08BSC	
H1	6.25	6.50	6.85
L	12.75	13.50	13.80
L1	-	3.10	3.40
ФР	3.40	3.60	3.80
Q	2.60	2.80	3.00

TO-220

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Revision history of JHB30N60EE2/JHG30N60EE2/JHH30N60EE2/JHP30N60EE2 Specification

Version	Change Items	Effective Date
1.00	Initial Release.	22-Jun-20
1.01	Thermal specification and package updates.	24-Jun-20



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